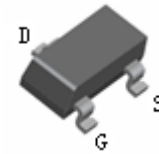


## FEATURES

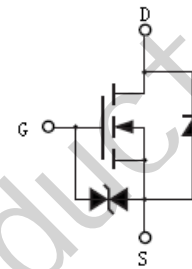
- Low on-resistance.
- High ESD.
- High-speed switching.
- Low-voltage drive(4V).
- Drive circuits can be simple.
- Parallel use is easy.



**SOT-23**

## APPLICATIONS

- N-channel enhancement mode effect transistor.
- Switching application.



## ORDERING INFORMATION

Type No.	Marking	Package Code
2N7002K	7002K	SOT-23

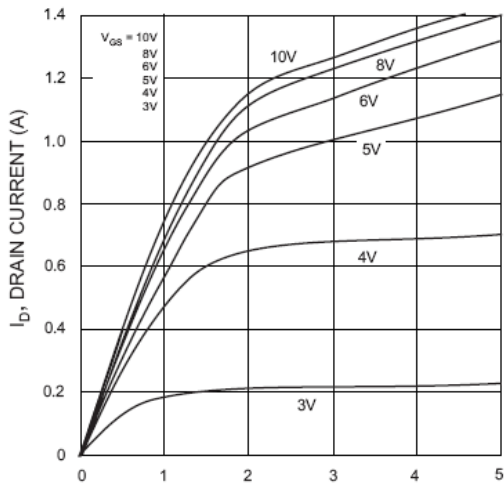
## MAXIMUM RATING @ Ta=25°C unless otherwise specified

Symbol	Parameter	Value	Units
$V_{DSS}$	Drain-Source voltage	63	V
$V_{GSS}$	Gate -Source voltage	$\pm 20$	V
$I_D$	Drain current	-continuous	$\pm 300$
		-Pulsed	$\pm 800$
$I_S$	Source current	-continuous	200
		-Pulsed	0.8
$P_D$	Power Dissipation	350	mW
$R_{\theta JA}$	Thermal Resistance,Junction to Ambient	357	$^{\circ}C/W$
$T_J, T_{stg}$	Junction and Storage Temperature	-65 to +150	$^{\circ}C$

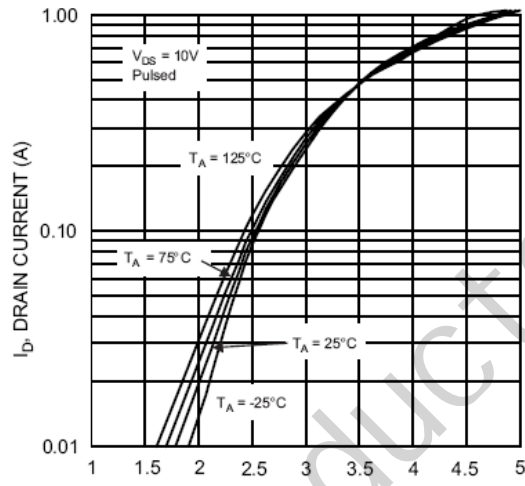
**ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified**

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Gate leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V			±6	μA
Forward voltage	V <sub>SD</sub>	I <sub>S</sub> =0.3A, V <sub>GS</sub> =0V			1.2	V
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	63			V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>DS</sub> =250μA	1.1		2.4	V
Drain cutoff Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V, V <sub>GS</sub> =0V			0.06	μA
Drain-source on-state resistance	R <sub>DS(on)</sub>	I <sub>D</sub> =0.05A, V <sub>GS</sub> =5V			7.5	Ω
		I <sub>D</sub> =0.5A, V <sub>GS</sub> =10V			7.5	
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =200mA	80			mS
Input capacitance	C <sub>ISS</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHz		33		pF
Output capacitance	C <sub>OSS</sub>			14		
Reverse transfer capacitance	C <sub>RSS</sub>			9		
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = 30V, I <sub>D</sub> = 150mA, R <sub>L</sub> = 200Ω, V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 10Ω		6		ns
Rise time	t <sub>R</sub>			5		ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			13		ns
Fall time	t <sub>F</sub>			80		ns
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> =30V, V <sub>GS</sub> =10V I <sub>D</sub> =200mA		3	6	nC
Gate-source charge	Q <sub>gs</sub>			0.6		nC
Gate-drain charge	Q <sub>gd</sub>			0.5		nC

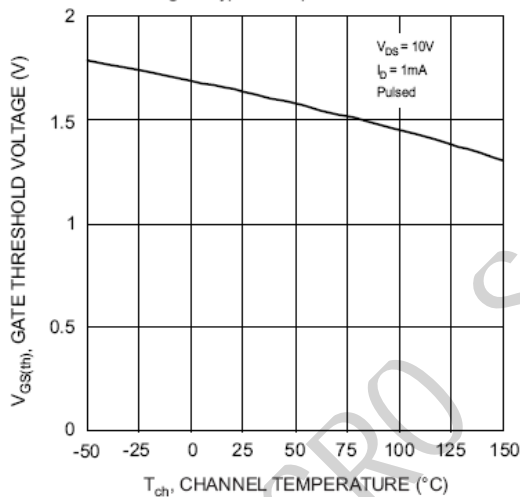
## TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V)  
 Fig. 1 Typical Output Characteristics



V<sub>GS</sub>, GATE-SOURCE VOLTAGE (V)  
 Fig. 2 Typical Transfer Characteristics



T<sub>ch</sub>, CHANNEL TEMPERATURE (°C)  
 Fig. 3 Gate Threshold Voltage vs. Channel Temperature

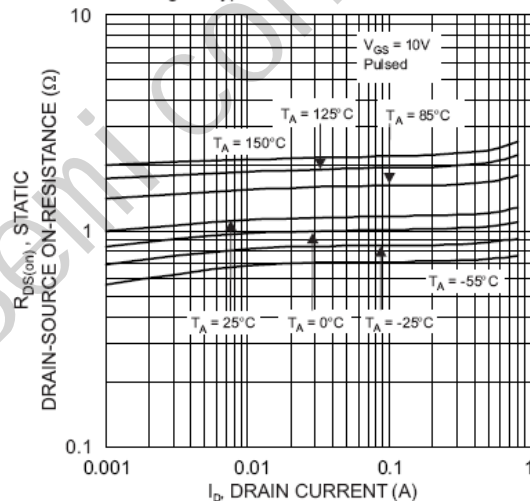
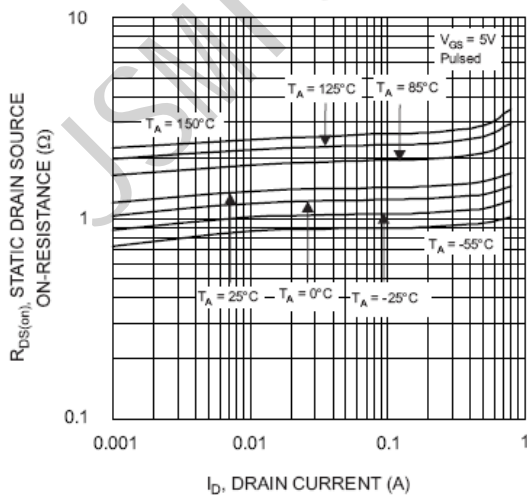
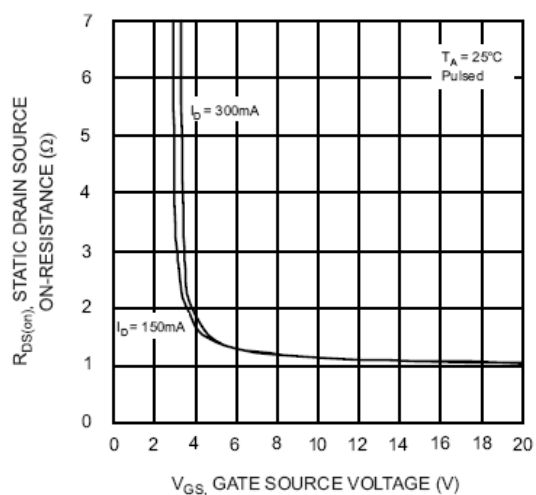


Fig. 4 Static Drain-Source On-Resistance Vs. Drain Current



I<sub>D</sub>, DRAIN CURRENT (A)  
 Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

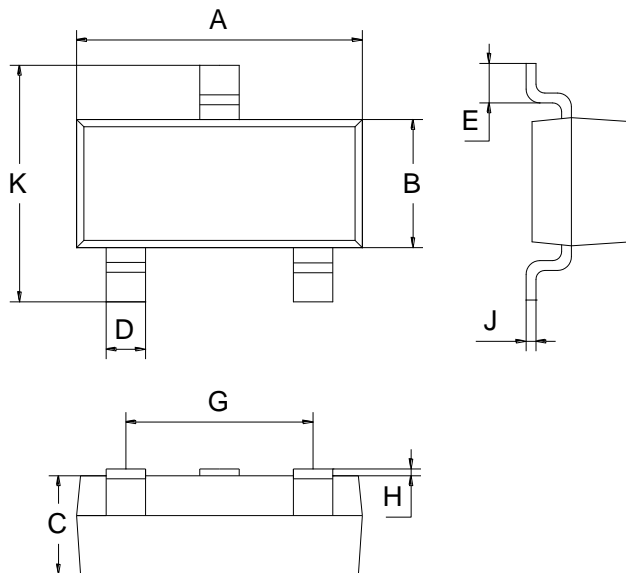


V<sub>GS</sub>, GATE SOURCE VOLTAGE (V)  
 Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

## PACKAGE OUTLINE

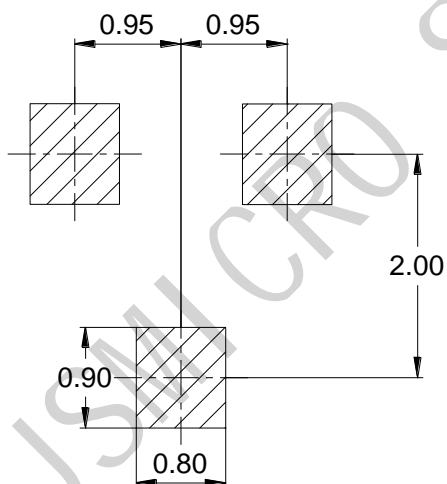
Plastic surface mounted package

SOT-23



SOT-23		
Dim	Min	Max
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60
All Dimensions in mm		

## SOLDERING FOOTPRINT



Unit: mm

## PACKAGE INFORMATION

Device	Package	Shipping
2N7002K	SOT-23	3000 pcs / Tape & Reel